

### General Description

These P-Channel enhancement mode power field effect transistors use advanced trench technology and design to provide excellent RDS(ON) . This device is suitable for use as a load switch or in PWM applications.

### Features

- Fast switching speed
- Lower On-resistance
- 100% EAS Guaranteed
- Simple Drive Requirement

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	-80	A
$I_{DM}$	Pulsed Drain Current	-240	A
EAS	Single Pulse Avalanche Energy	480	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	150	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (Drain)	---	1.0	$^\circ\text{C/W}$

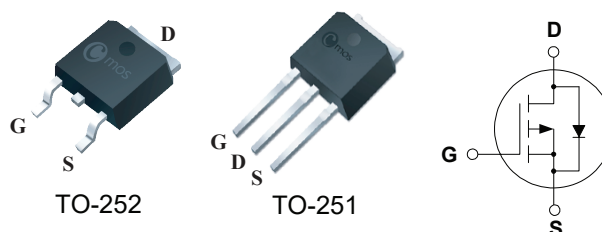
### Product Summary

BVDSS	RDSON	ID
-60V	14m $\Omega$	-80A

### Applications

- DC-DC Converters
- Load Switches
- BLDC Motor driver

### TO-252 / 251 Pin Configuration



Type	Package	Marking
CMD80P06	TO-252	CMD80P06
CMU80P06	TO-251	CMU80P06

### Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$ , $I_D=-28A$	---	---	14	$m\Omega$
		$V_{GS}=-4.5V$ , $I_D=-20A$	---	---	18	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu A$	-1.0	---	-3.0	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-48V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	-1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-10V$ , $I_D=-20A$	---	40	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	2.5	---	$\Omega$
$Q_g$	Total Gate Charge	$V_{DD}=-30V$ , $I_D=-20A$ $V_{GS}=-10V$	---	62	---	nC
$Q_{gs}$	Gate-Source Charge		---	9	---	
$Q_{gd}$	Gate-Drain Charge		---	15	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V$ , $V_{GS}=-10V$ , $R_L=1.5\Omega$ $R_G=3\Omega$	---	17	---	ns
$T_r$	Rise Time		---	19	---	
$T_{d(off)}$	Turn-Off Delay Time		---	54	---	
$T_f$	Fall Time		---	34	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-30V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	8000	---	pF
$C_{oss}$	Output Capacitance		---	356	---	
$C_{rss}$	Reverse Transfer Capacitance		---	265	---	

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-80	A
$I_{SM}$	Pulsed Source Current		---	---	-240	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V$ , $I_F=-28A$	---	---	-1.2	V

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